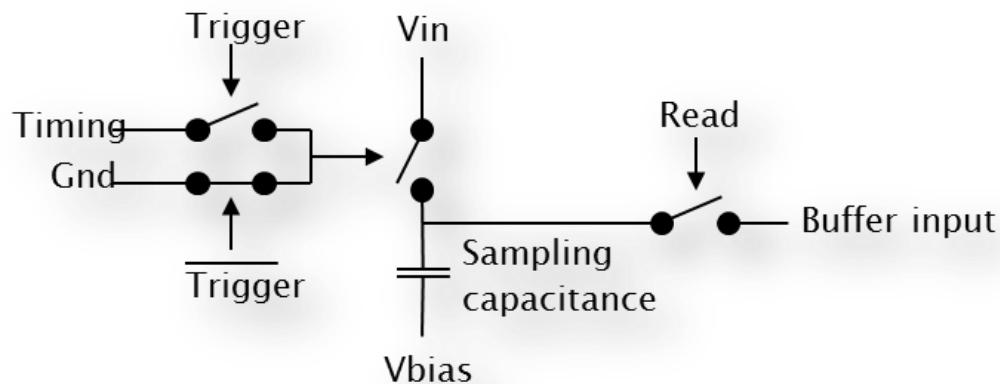


# Sampling cell – Dynamic range – Analog bandwidth

Hervé Grabas

# Sampling cell – Principle

- ▶ An unit is basically made of one storage capacitance controlled by two signals :
  - -Timing (800ps wide pulse).
  - -Trigger (in case of an event).
- ▶ Timing stores the analog values in the sampling capacitance at a rate of 15Gs/s.
- ▶ Trigger open all the write switches in case of an event at the input.

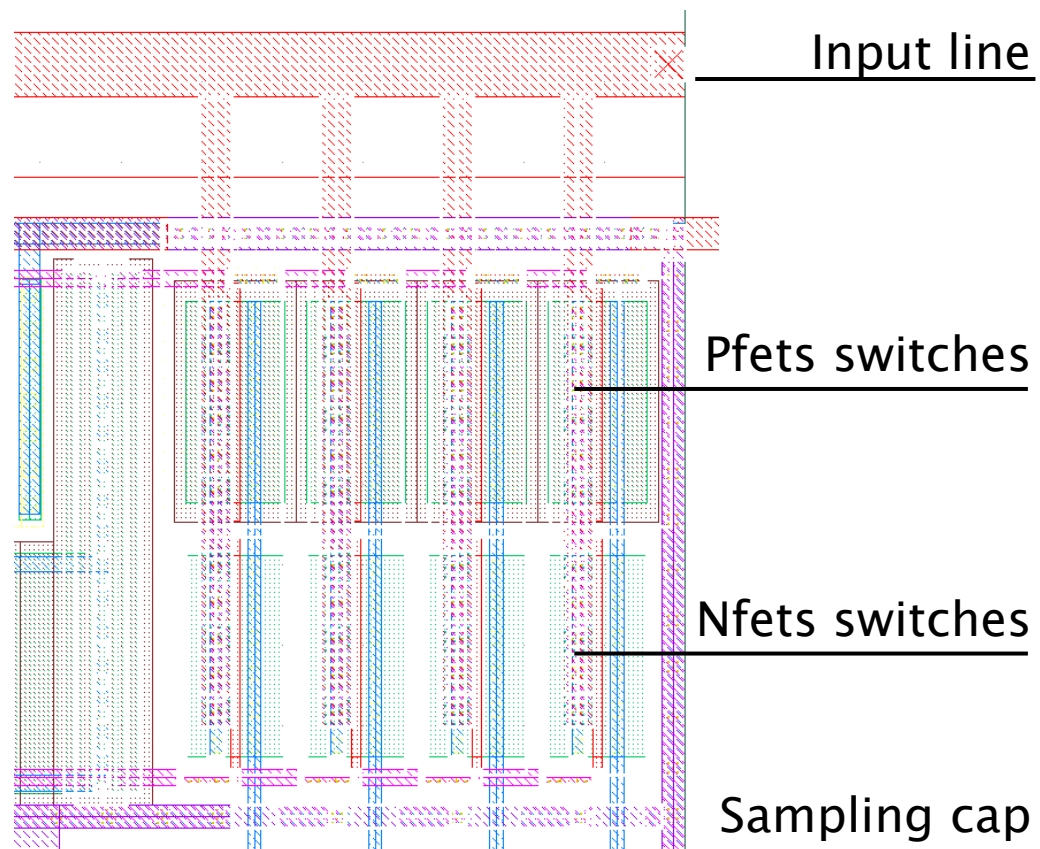


Nota: in case of this diagram Timing is active high.



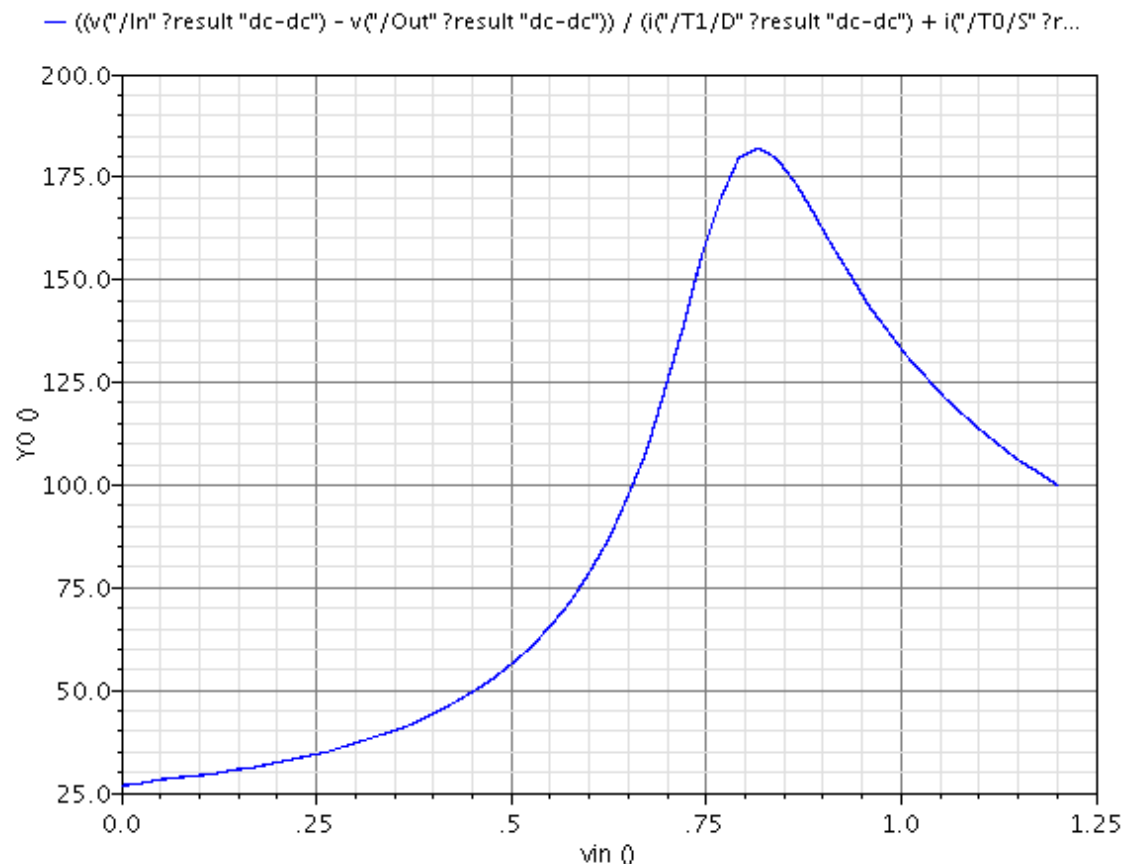
# Sampling cell – Input switch size

- ▶ Input switch size:  $10\mu\text{m} \times 120\text{nm}$ .





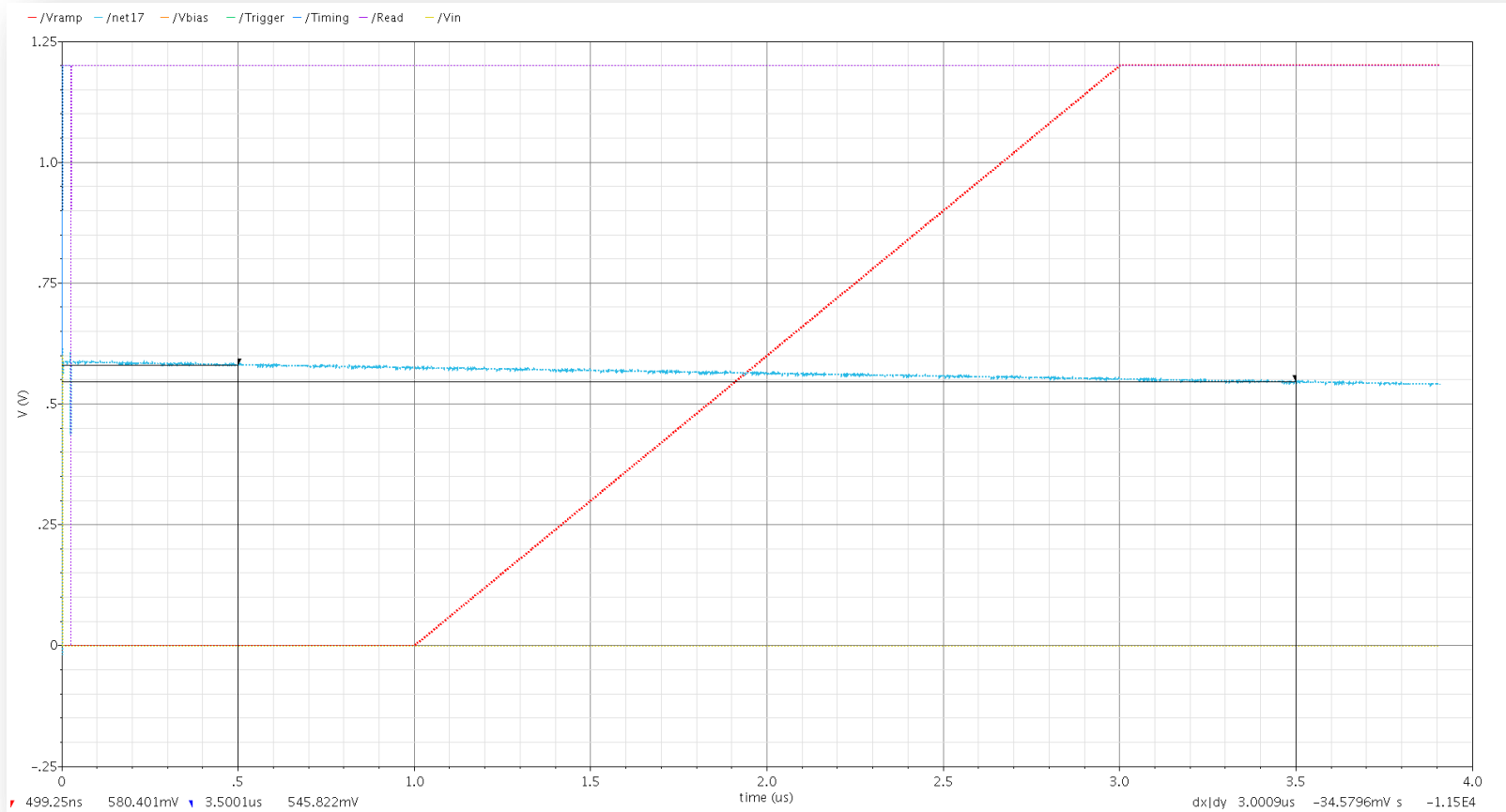
# Sampling cell – Input switch Ron



The Ron resistance is Voltage dependent. Therefore the rise time will be amplitude dependent inside the cell.  $R_{on} \sim 100\Omega$



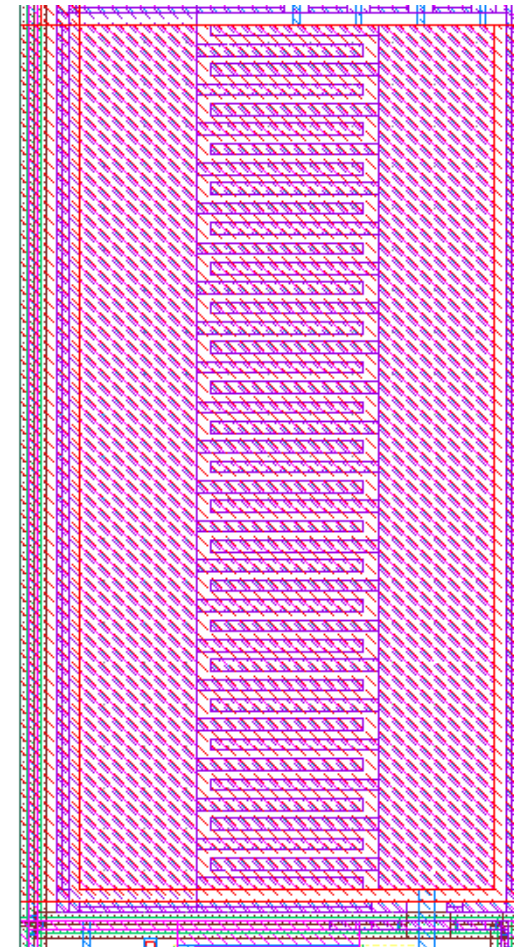
# Switch leakage



Voltage drop: 35mV in 3us.  
Leackage current: 600pA.

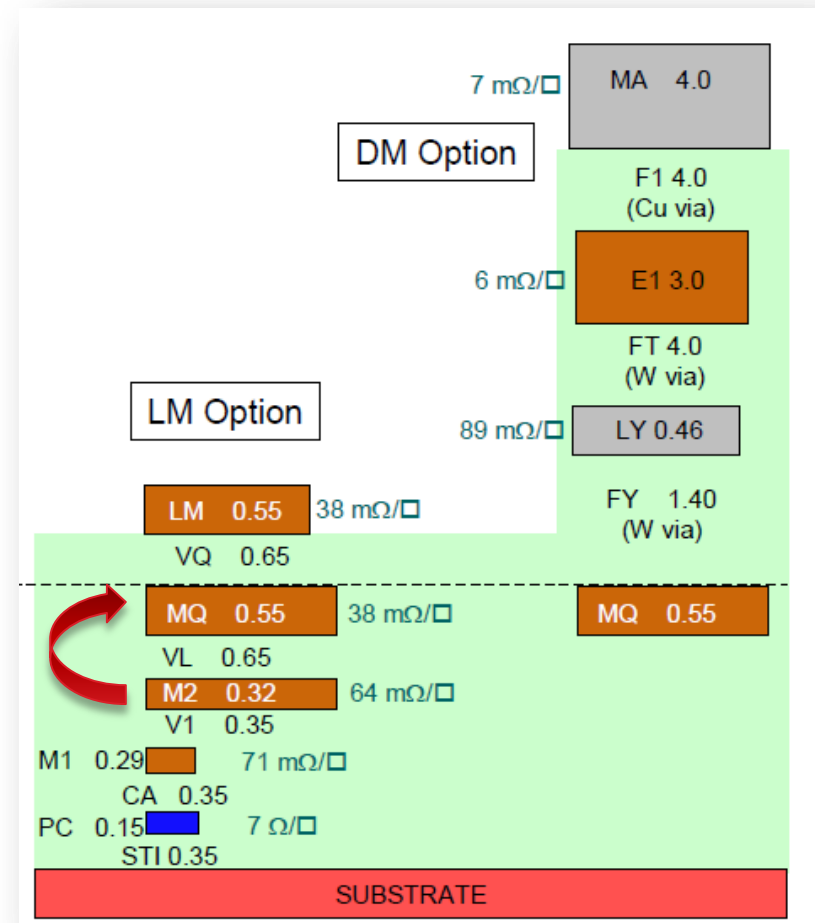
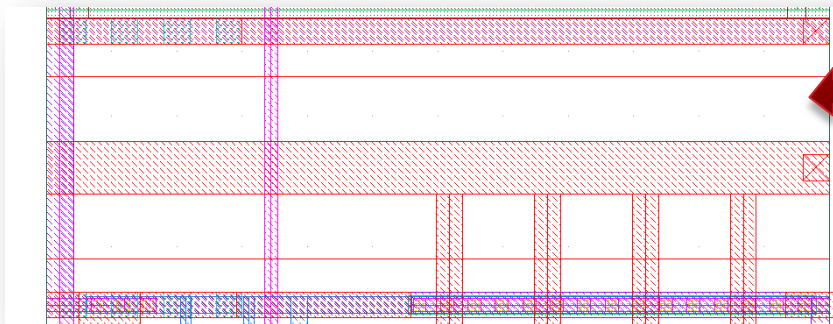
# Sampling cell – Capacitance

- ▶ Sampling capacitance: 60fF after extraction.
- ▶ Interdigitated layout with three levels of metals (M1, M2, M3).
- ▶ Shielding
  - Top shielding in MQ.
  - Side shielding in M1, M2, M3, MQ.



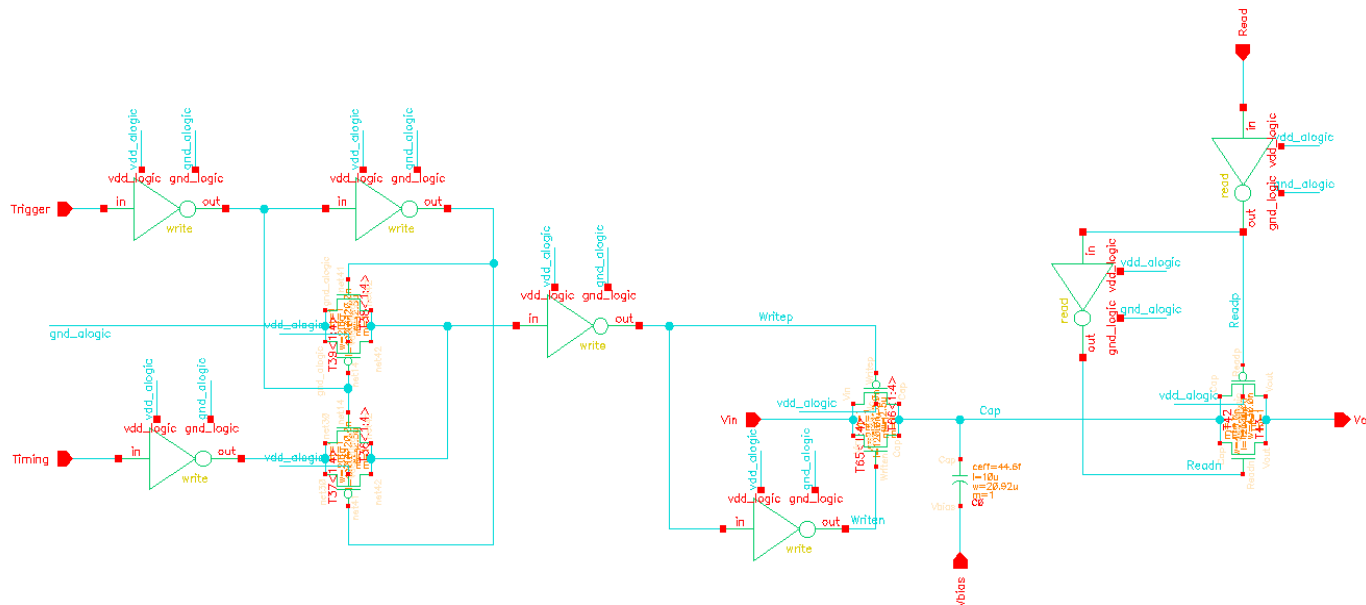
# Input line improvements

- ▶ Went from M3 to MQ (gain a factor 2 in lin.res.).
- ▶ Add anti-fill layers, for layers from M1 to MG.
- ▶ Increase the width.



# Sampling cell – Schematic

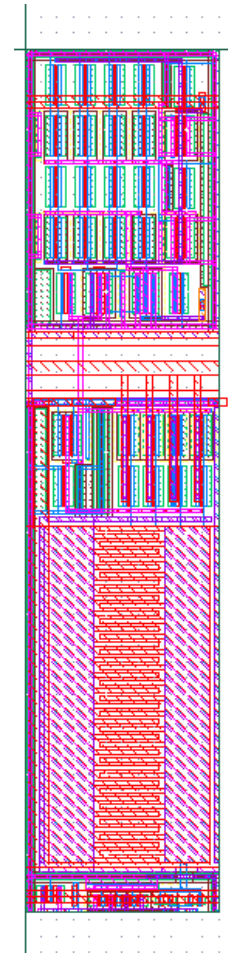
- ▶ Separate analogic vdd and analogic gnd.
- ▶ Regenerative buffers for every input signals (Timing, Trigger, Read, Write).





# Sampling cell – Layout

- ▶ Size:  $12\mu\text{m} \times 55\mu\text{m}$ .
- ▶ Input line in MG :  $800\text{nm} \times 3.072\text{mm}$ .
- ▶ Input line resistance:  $38\mu\Omega/\square$ .
- ▶ Total input line resistance:  $.146\Omega$ .
- ▶ Total input line capacitance:  $1.5\text{pF}$  (without including the pad).
- ▶ The sampling has 2 poles:
  - $1/(2 \times \pi \times 50\Omega \times 1.5\text{pF}) = 2\text{GHz}$ . (input line)
  - $1/(2 \times \pi \times 100\Omega \times 60\text{fF}) = 20\text{GHz}$ . (sampling cap)







# The $50\Omega$ input resistance

- ▶ The input line coming from the detector is a  $50\Omega$  transmission line.
- ▶ There is three possibilities for the terminaison:
  - On board
  - On chip after the pads
  - On chip at the end of the 256 cells.

# The 50Ω input resistance (2)

	Advantages	Disadvantages
On the board	<ul style="list-style-type: none"> <li>• Can be replaced</li> <li>• Possibility of a good transmission line until the termination.</li> </ul>	<ul style="list-style-type: none"> <li>• The pad capacitance ~3pF and input line cap ~1.5pF are in series with 50Ω.</li> <li>• Bwth &lt;1GHz</li> </ul>
After the pad	<ul style="list-style-type: none"> <li>• Input signal won't see the pad input cap.</li> <li>• Bandwidth 1–2GHz.</li> </ul>	<ul style="list-style-type: none"> <li>• Non replaceable.</li> <li>• More impedance mismatch at the input of the chip.</li> </ul>
After the transmission line	<ul style="list-style-type: none"> <li>• Maximum bandwidth possible.</li> </ul>	<ul style="list-style-type: none"> <li>• Non replaceable</li> <li>• Potential drop of tension across the input line (Res = .1Ω) ?</li> </ul>

# The 50 $\Omega$ input resistance

- ▶ 4 channels with 50 $\Omega$  outside the chip.
- ▶ 2 test channels with 50 $\Omega$  at the end of the line.